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## 2SK1103

### Silicon N-channel junction FET

For switching circuits
Complementary to 2SJ0163

#### ■ Features

- Low ON resistance
- Low-noise characteristics

#### ■ Absolute Maximum Ratings T<sub>a</sub> = 25°C

| Parameter                    | Symbol           | Rating      | Unit |
|------------------------------|------------------|-------------|------|
| Gate-drain surrender voltage | V <sub>GDS</sub> | -65         | V    |
| Drain current                | $I_{D}$          | 20          | mA   |
| Gate current                 | $I_G$            | 10          | mA   |
| Power dissipation            | $P_{\mathrm{D}}$ | 150         | mW   |
| Channel temperature          | T <sub>ch</sub>  | 150         | °C   |
| Storage temperature          | T <sub>stg</sub> | -55 to +150 | °C   |

#### Package

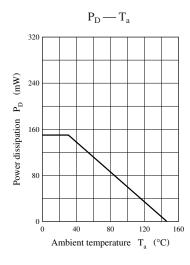
- Code
  - Mini3-G1
- Pin Name
  - 1: Source
  - 2: Drain
  - 3: Gate
- Marking Symbol: 4L

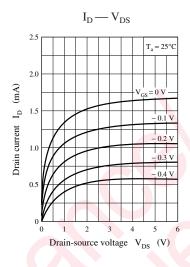
### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

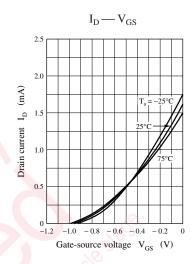
| Parameter                                  | Symbol              | Conditions   | Min | Тур  | Max  | Unit |
|--|---------------------|--|-----|------|------|------|
| Gate-drain surrender voltage               | V <sub>GDS</sub>    | $I_G = -10 \mu\text{A},  V_{DS} = 0$                           | -65 | Olle |      | V    |
| Drain-source current *                     | $I_{DSS}$           | $V_{DS} = 10 \text{ V}, V_{GS} = 0$                            | 0.6 | 55   | 6.0  | mA   |
| Gate-source cutoff current                 | $I_{GSS}$           | $V_{GS} = -30 \text{ V}, V_{DS} = 0$                           | 6   |      | -10  | nA   |
| Gate-source cutoff voltage                 | $V_{GSC}$           | $V_{DS} = 10 \text{ V}, I_{D} = 10 \mu A$                      | 0.7 | -1.5 | -3.5 | V    |
| Forward transfer admittance                | Y <sub>fs</sub>     | $V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}, f = 1 \text{ kHz}$ | 1.8 | 2.5  |      | mS   |
| Drain-source ON resistance                 | R <sub>DS(on)</sub> | $V_{DS} = 10 \text{ mV}, V_{GS} = 0$                           |     | 300  |      | Ω    |
| Short-circuit forward transfer capacitance | C <sub>iss</sub>    | $V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$         |     | 7    |      | pF   |
| (Common source)                            |                     | is un  |     |      |      |      |
| Reverse transfer capacitance               | C <sub>rss</sub>    |  |     | 1.5  |      | pF   |
| (Common source)                            |                     | So Ville   |     |      |      |      |

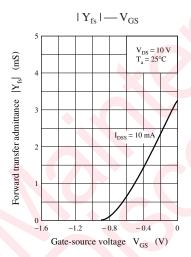
- Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
  - 2. Observe precautions for handling. Electrostatic sensitive devices.
  - 3. \*: Rank classification

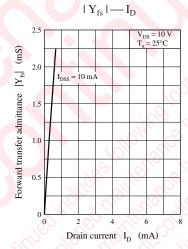
| Rank                  | Р          | Q          | R          |
|-----------------------|------------|------------|------------|
| I <sub>DSS</sub> (mA) | 0.6 to 1.5 | 1.0 to 3.0 | 2.5 to 6.0 |

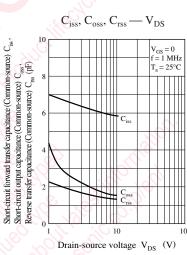






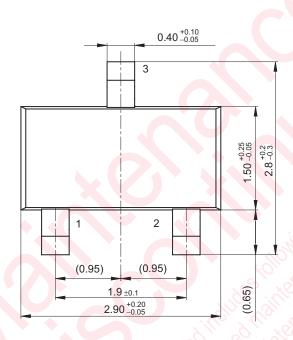


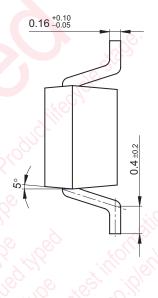


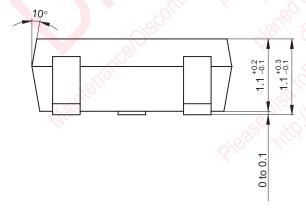


2 SJF00011DED

Mini3-G1 Unit: mm







SJF00011DED 3

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